

Controllable Synthesis of Conjugated Thiophenylethyne-based Compounds with Different Chain Lengths

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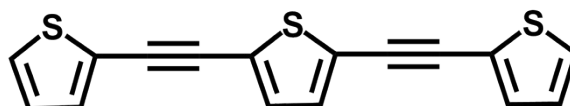
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Supporting Information

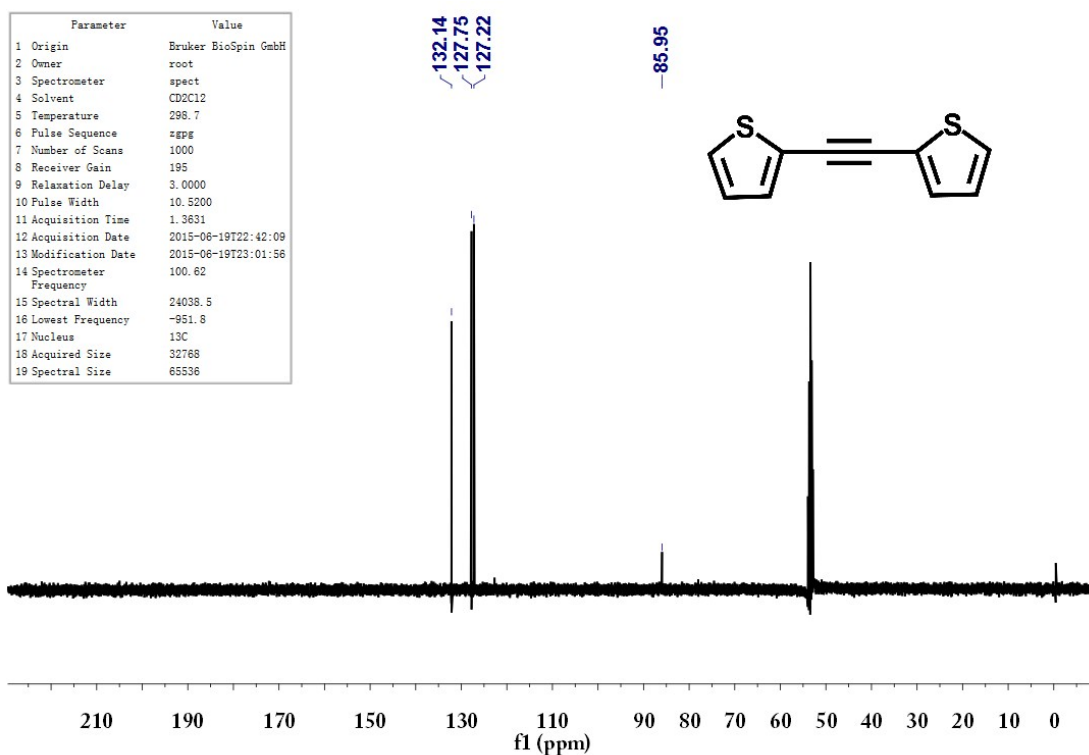
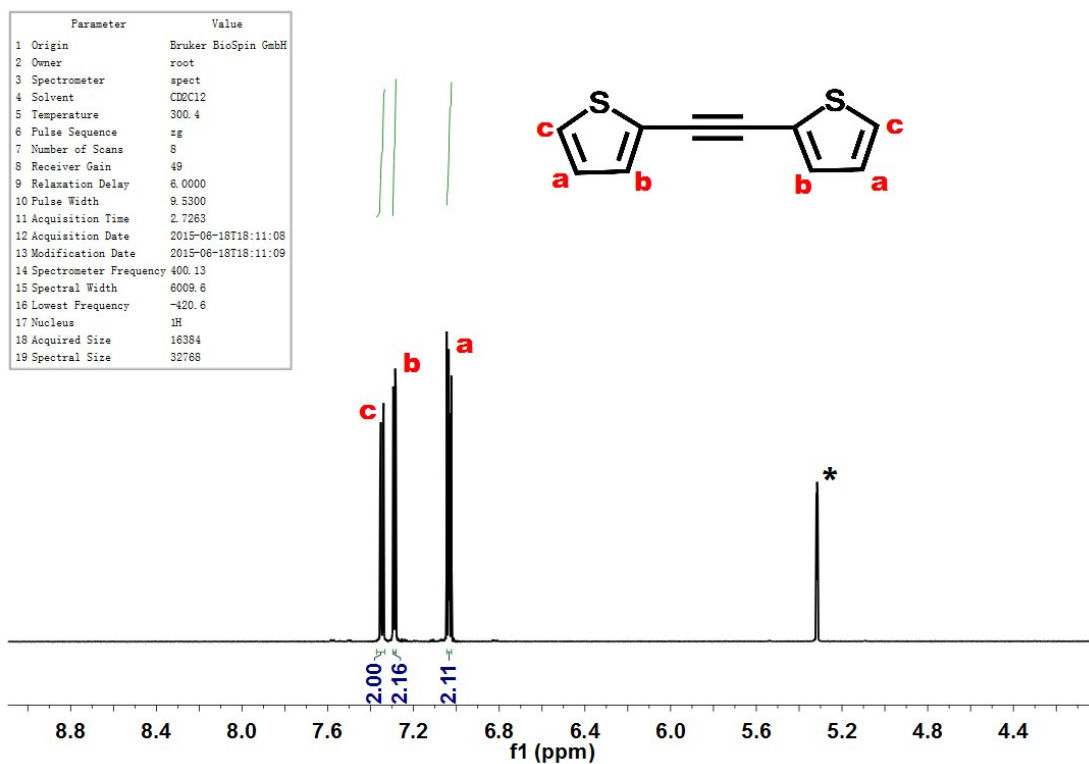
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Table S1 Summary of crystal data and reflective collection parameters for **2**.



| | |
|---|---|
| Empirical formula | C ₁₆ H ₈ S ₃ |
| Formula weight | 296.40 |
| Crystal size, mm | 0.26 x 0.21 x 0.17 |
| Crystal system | Monoclinic, C2/c |
| space group | P2(1)/c |
| a, Å | 15.042(5) |
| b, Å | 11.404(4) |
| c, Å | c = 32.856(10) |
| a, deg | 90 |
| β, deg | 95.094(5) |
| γ, deg | 90 |
| V, Å ³ | 5614(3) |
| Z | 16 |
| Calculated density, Mg/m ³ | 1.403 |
| F(000) | 2432 |
| Temperature, K | 296(2) |
| Wavelength, Å | 0.71073 |
| μ(Mo Ka), mm ⁻¹ | 0.509 |
| 2θ _{max} , deg (Completeness) | 25.00 (98.5 %) |
| no. of collected reflections | 13829 |
| no. of unique ref.(R _{int}) | 4882 (0.0618) |
| Data/restraints/parameters | 4882 / 7 / 352 |
| R ₁ , wR ₂ [obs I>2σ (I)] | 0.0881, 0.1980 |
| R ₁ , wR ₂ (all data) | 0.1181, 0.2094 |
| residual peak/hole, e. Å ⁻³ | 0.634 / -0.752 |
| transmission ratio | 0.9185/ 0.8791 |
| Goodness-of-fit on F ² | 1.067 |



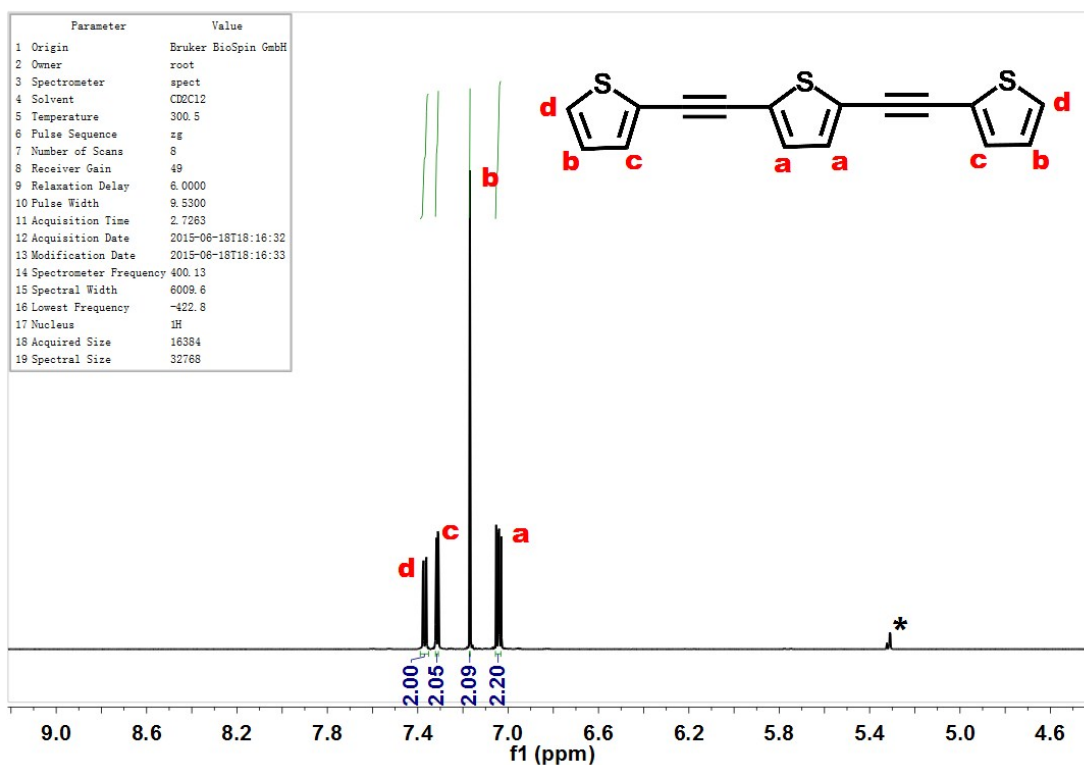


Fig. S3 The ¹H NMR spectrum of 2.

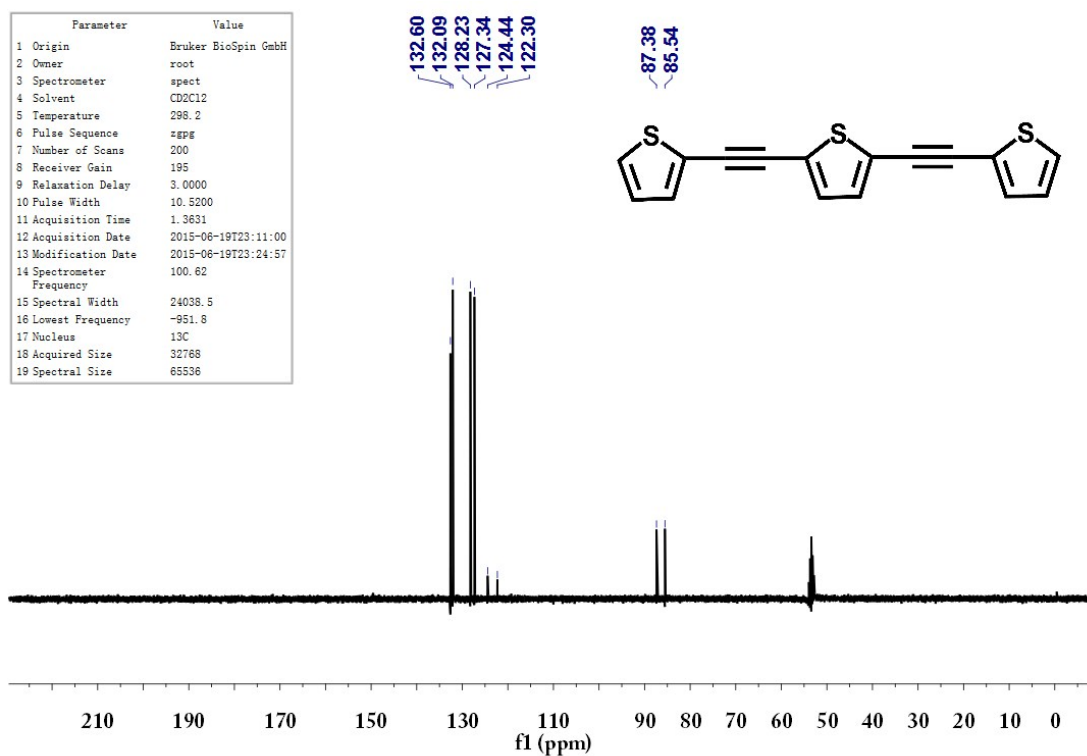
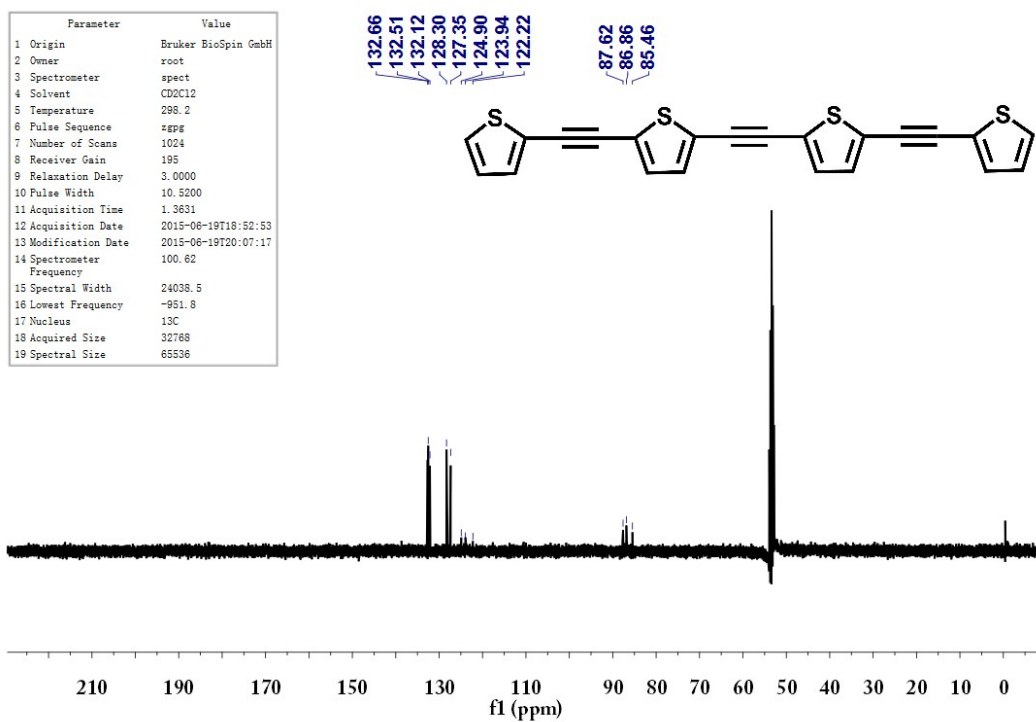
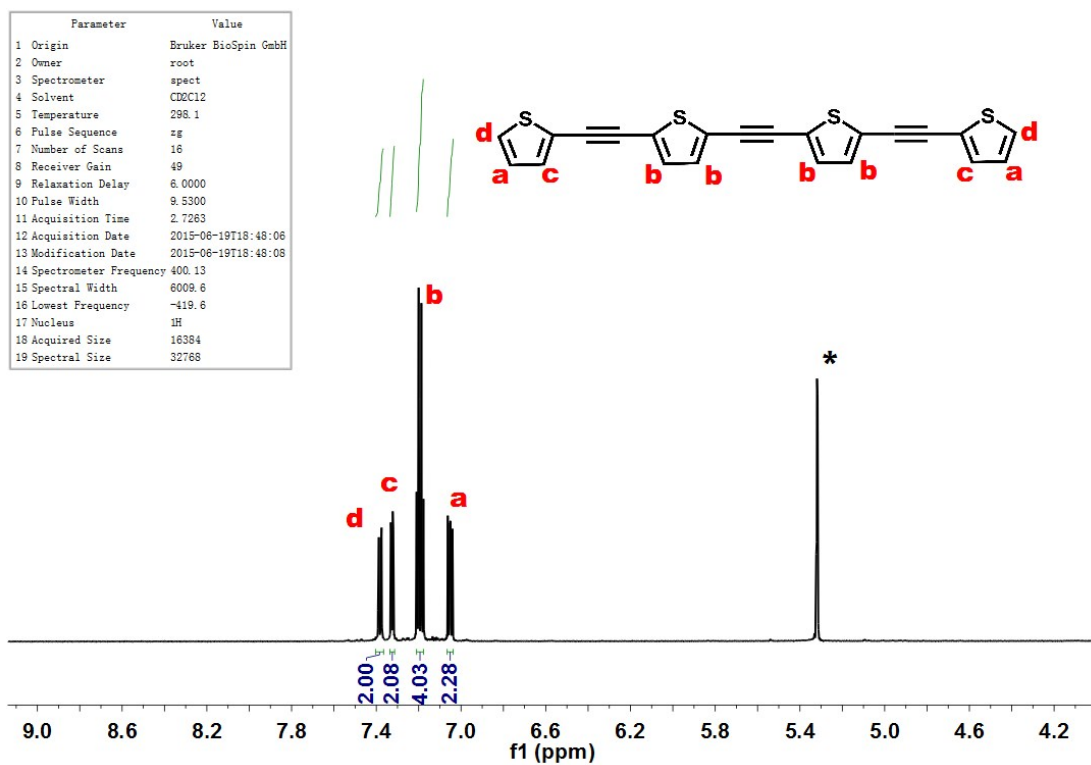


Fig. S4 The ¹³C NMR spectrum of 2.



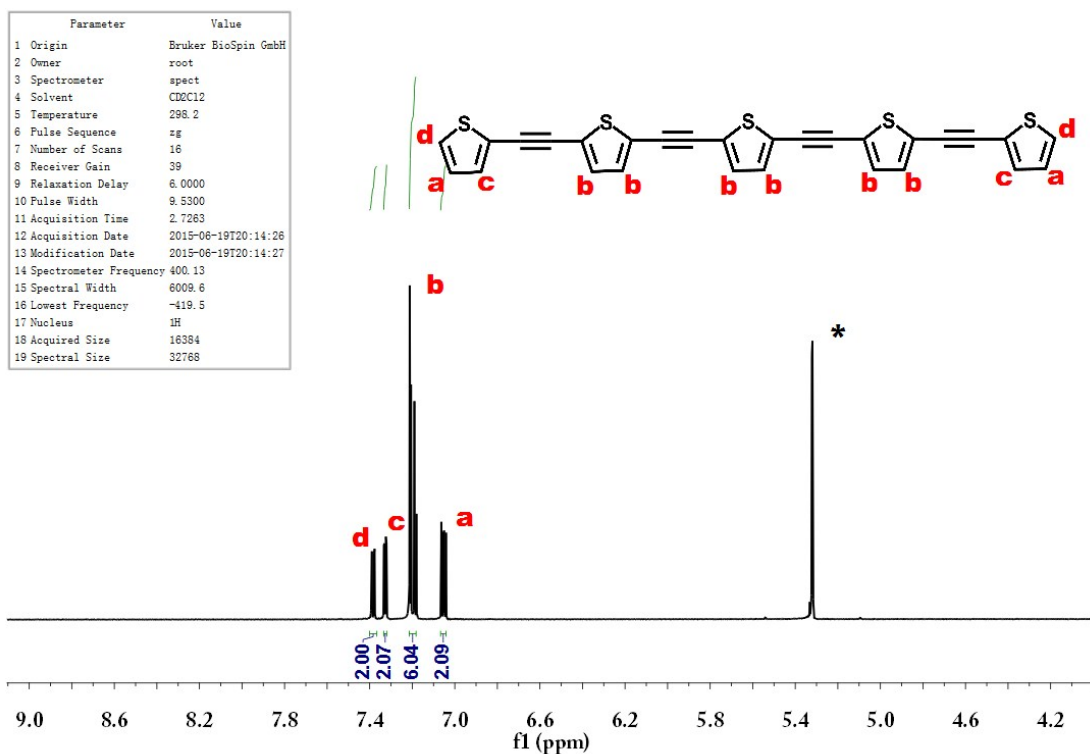


Fig. S7 The ¹H NMR spectrum of 4.

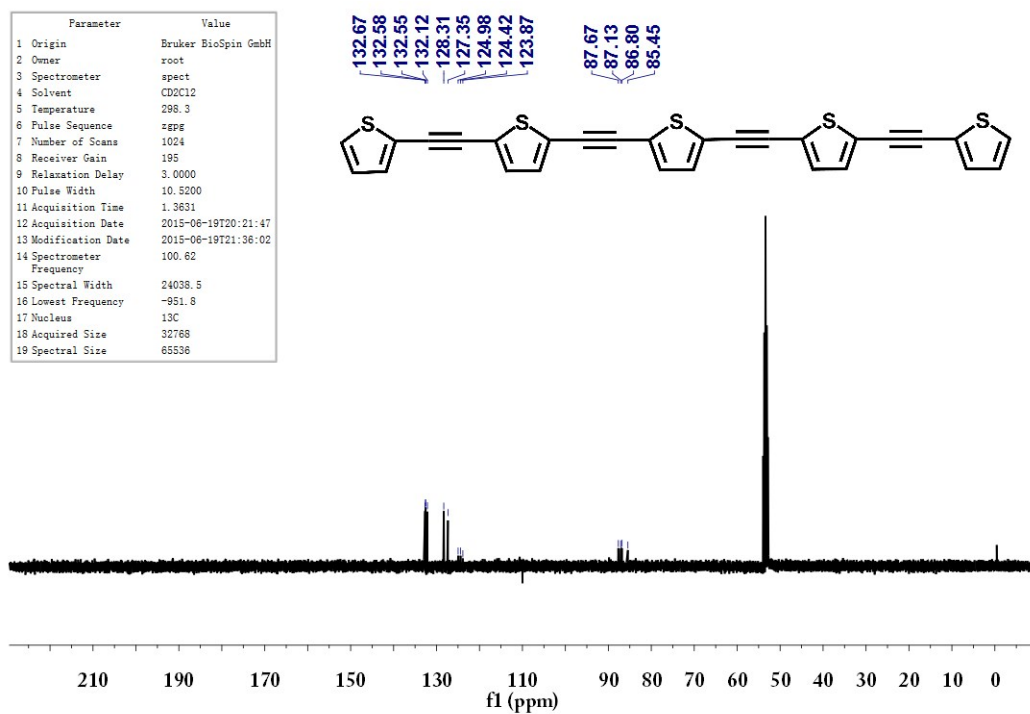


Fig. S8 The ¹³C NMR spectrum of 4.

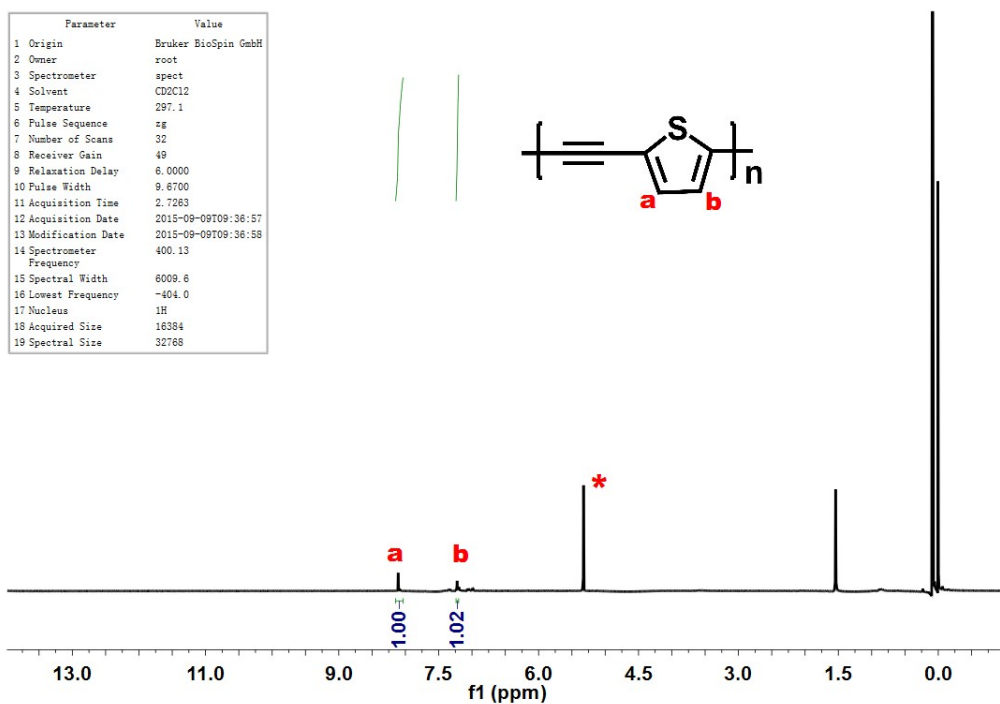


Fig. S9 The ^1H NMR spectrum of PTE

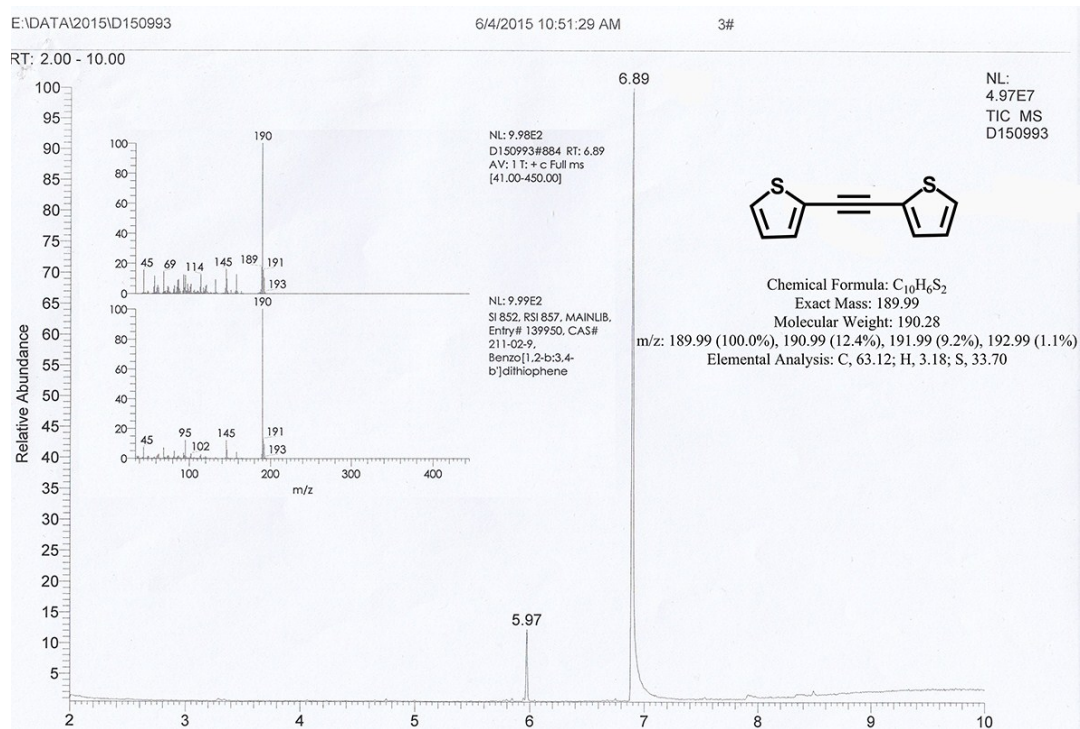


Fig. S10 The MALDI-TOF of 1.

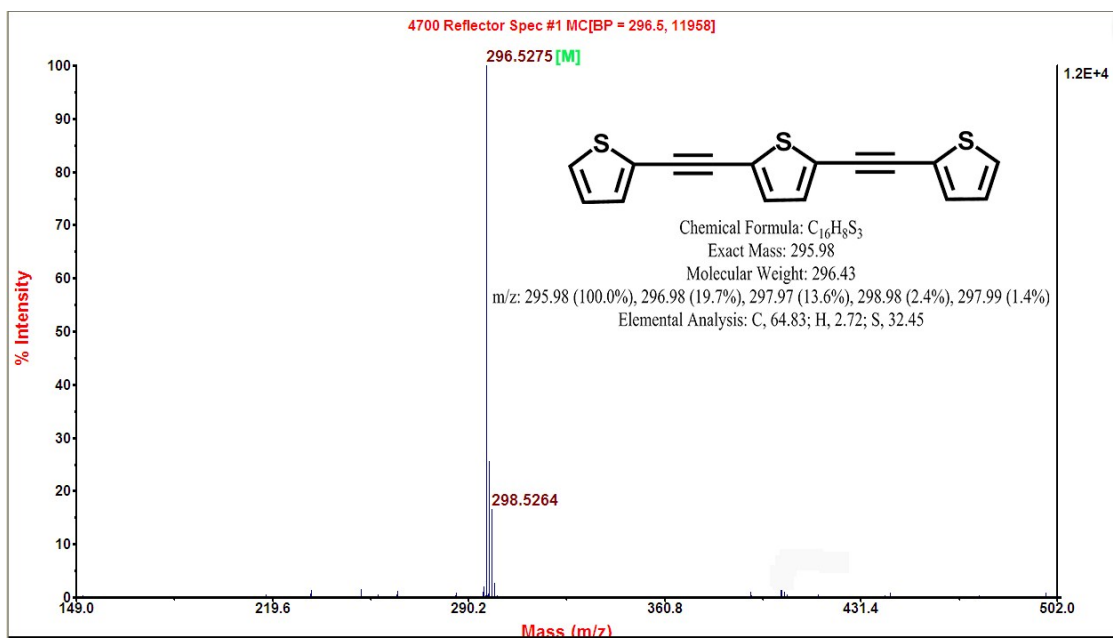


Fig. S11 The MALDI-TOF of 2.

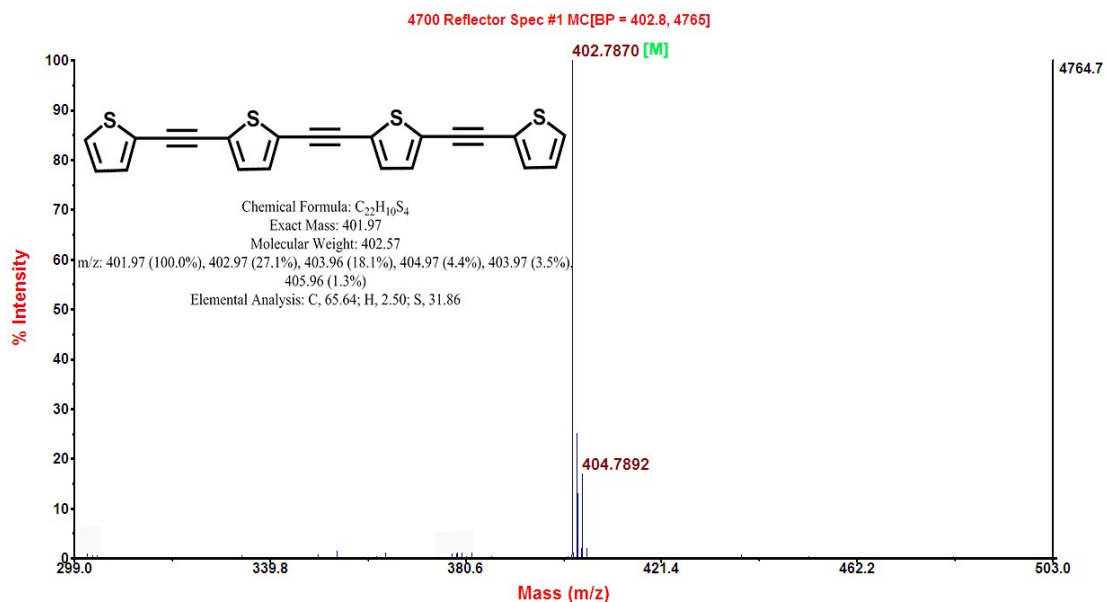


Fig. S12 The MALDI-TOF of 3.

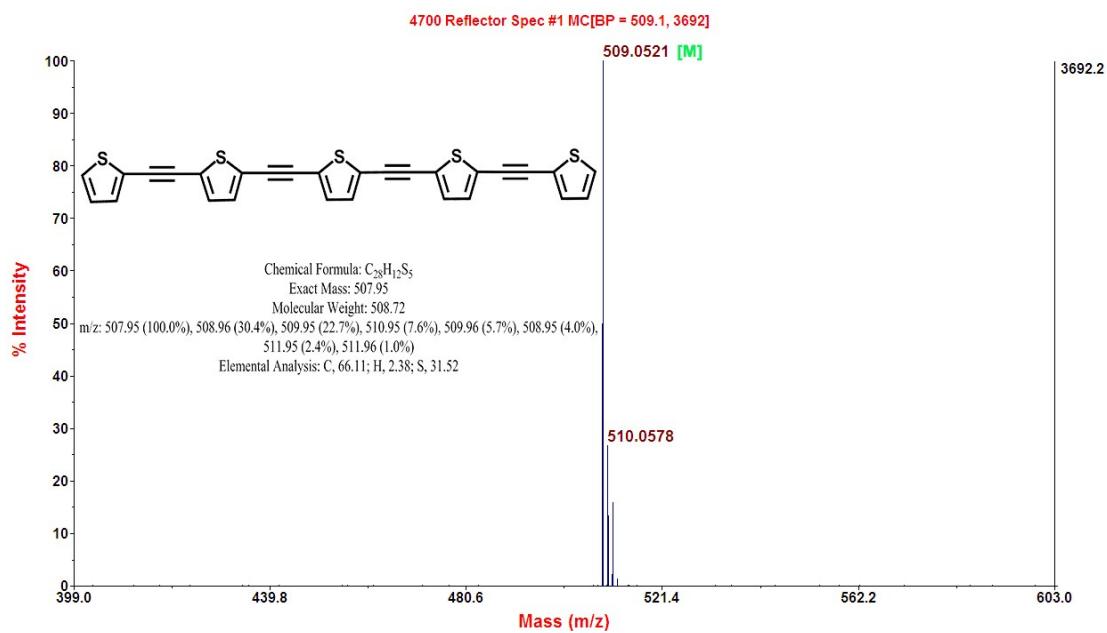


Fig. S13 The MALDI-TOF of 4.

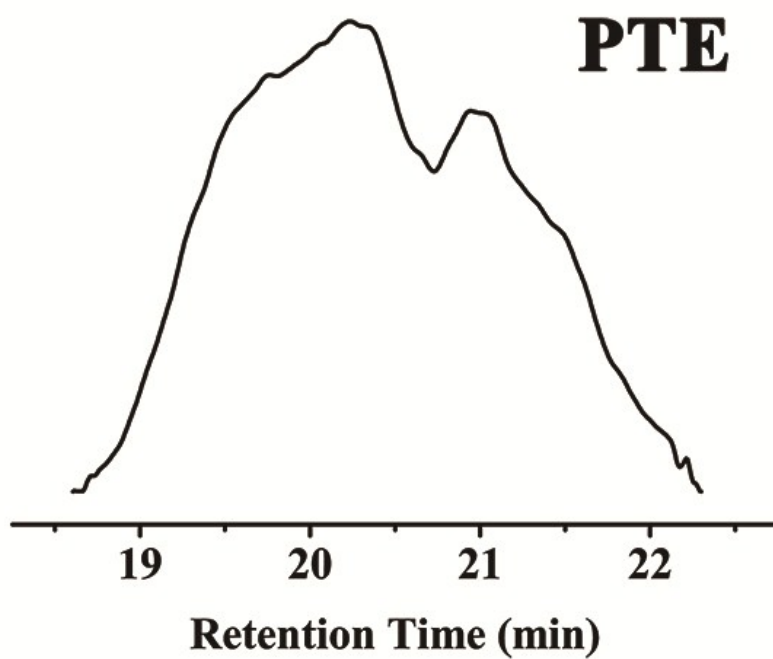


Fig. S14 The GPC data of PTE.

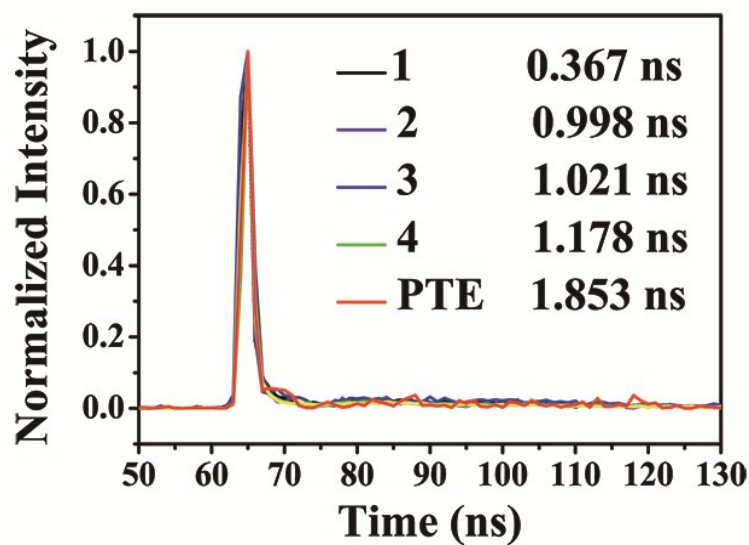


Fig. S15 The fluorescence lifetime of 1-4 and PTE in CH_2Cl_2 solutions.

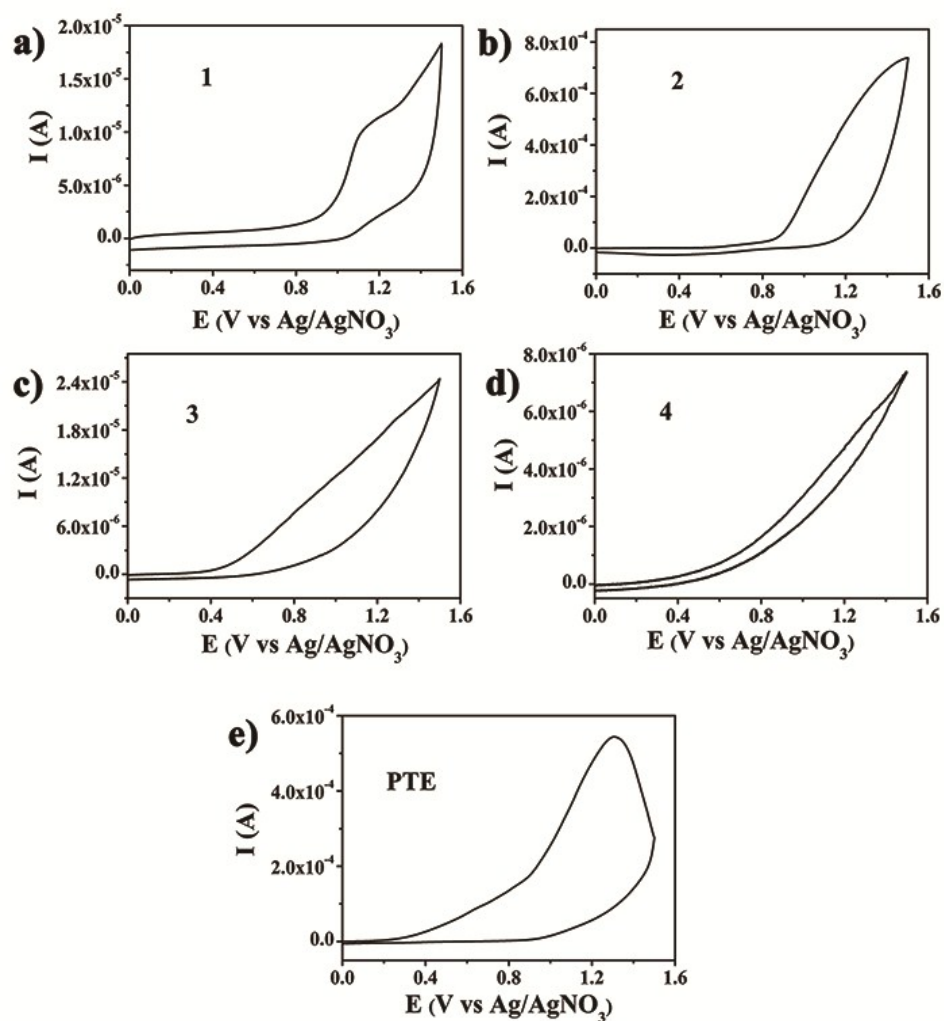


Fig. S16 The CV curves of (a) 1, (b) 2, (c) 3, (d) 4 and (e) PTE in CH_2Cl_2 solution.

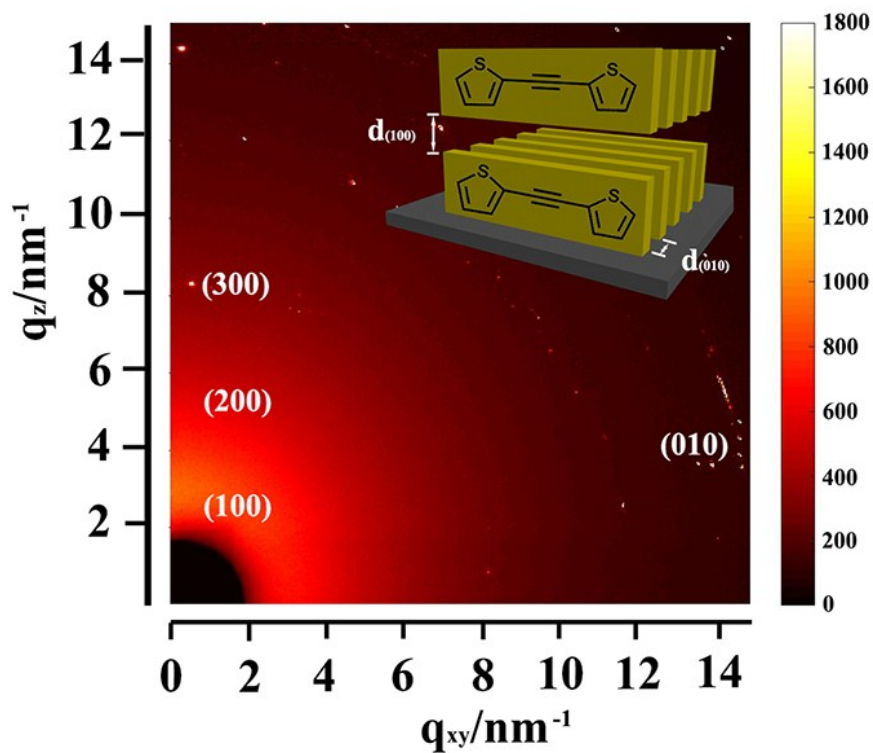


Fig. S17 The 2D-GIXRD patterns of 1. The inserted model is a schematic diagram of the orientations of the aggregation structure with respect to the substrate in the films.

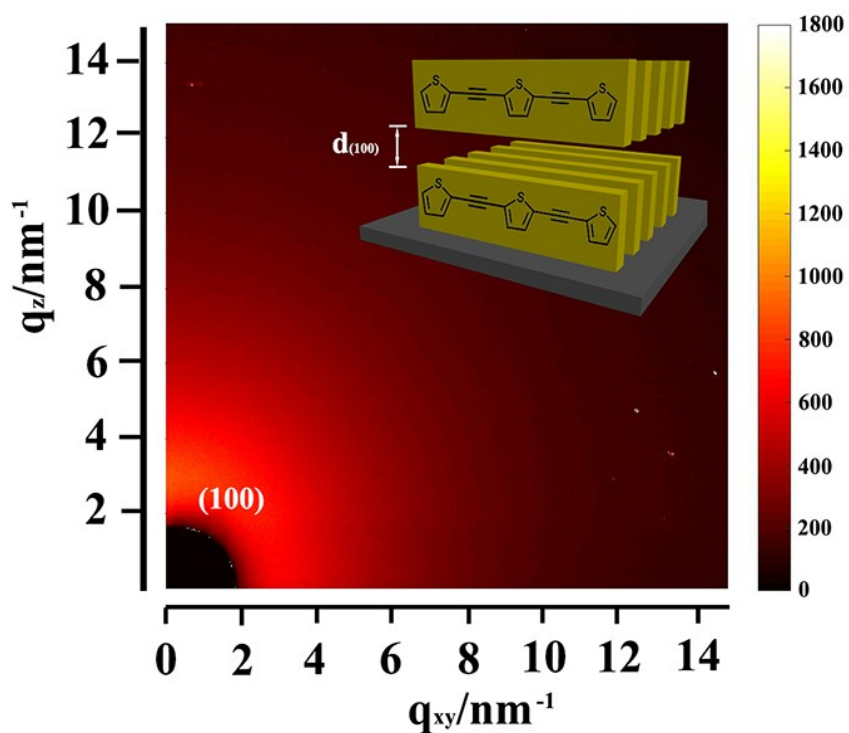


Fig. S18 The 2D-GIXRD patterns of 2. The inserted model is a schematic diagram of the orientations of the aggregation structure with respect to the substrate in the films.

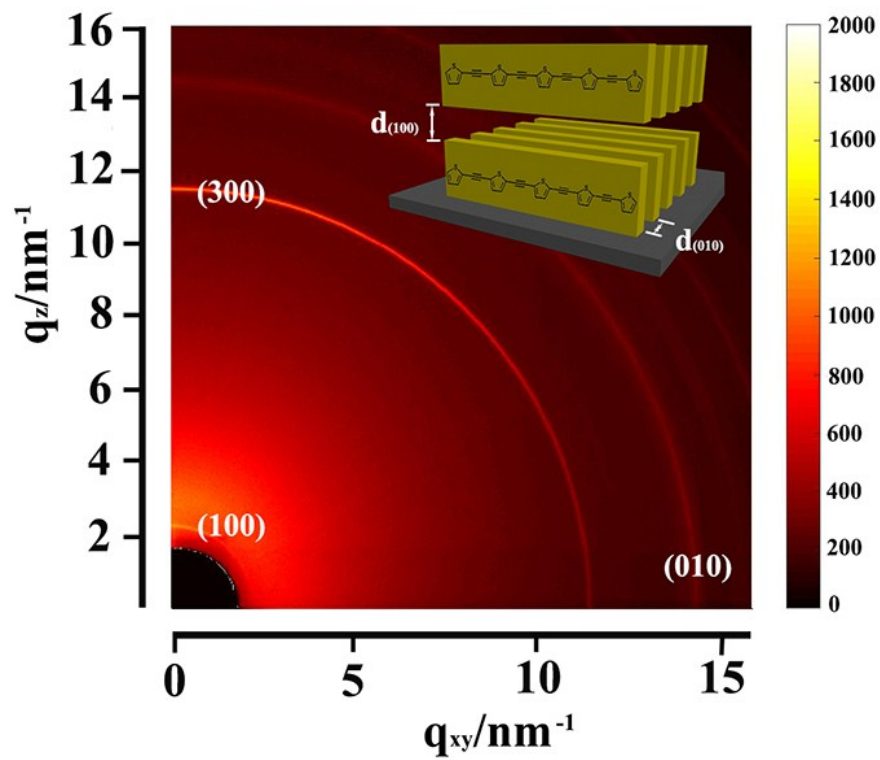


Fig. S19 The 2D-GIXRD patterns of 4. The inserted model is a schematic diagram of the orientations of the aggregation structure with respect to the substrate in the films.

The detailed calculated procedures for the charge carrier mobility.

According to the obtained V_{th} values and the metal-oxide semiconductor FET formula for the saturation regime, $I_{DS} = \frac{\mu WC_i}{2L} (V_G - V_{th})^2$, the calculations of the charge carrier mobility (μ) are below:

3

$$I_{DS} = 30.79 \times 10^{-6} \text{ A}, V_G = -6.69 \text{ V}, V_{DS} = 1 \text{ V}, C_i = 20 \text{ } \mu\text{F/cm}^2, W = 1 \text{ mm}, L = 1 \text{ mm}, V_{th} = -1.81 \text{ V}$$

$$\begin{aligned} \mu &= 2LI_{DS} / [WC_i(V_G - V_{th})^2] = 2I_{DS} / [C_i(V_G - V_{th})^2] \\ &= 2 \times 30.79 \times 10^{-7} / [20 \times 10^{-6} \times (-6.69 + 1.81)^2] \\ &= 0.13 \text{ cm}^2 \text{V}^{-1} \text{S}^{-1} \end{aligned}$$

4

$$I_{DS} = 35.93 \times 10^{-6} \text{ A}, V_G = -6.23 \text{ V}, V_{DS} = 1 \text{ V}, C_i = 20 \text{ } \mu\text{F/cm}^2, W = 1 \text{ mm}, L = 1 \text{ mm}, V_{th} = -2.14 \text{ V}$$

$$\begin{aligned} \mu &= 2LI_{DS} / [WC_i(V_G - V_{th})^2] = 2I_{DS} / [C_i(V_G - V_{th})^2] \\ &= 2 \times 35.93 \times 10^{-7} / [20 \times 10^{-6} \times (-6.23 + 2.14)^2] \\ &= 0.22 \text{ cm}^2 \text{V}^{-1} \text{S}^{-1} \end{aligned}$$

PTE

$$I_{DS} = 39.27 \times 10^{-6} \text{ A}, V_G = -5.27 \text{ V}, V_{DS} = 1 \text{ V}, C_i = 20 \text{ } \mu\text{F/cm}^2, W = 1 \text{ mm}, L = 1 \text{ mm}, V_{th} = -2.22 \text{ V}$$

$$\begin{aligned} \mu &= 2LI_{DS} / [WC_i(V_G - V_{th})^2] = 2I_{DS} / [C_i(V_G - V_{th})^2] \\ &= 2 \times 39.27 \times 10^{-7} / [20 \times 10^{-6} \times (-5.27 + 2.22)^2] \\ &= 0.42 \text{ cm}^2 \text{V}^{-1} \text{S}^{-1} \end{aligned}$$

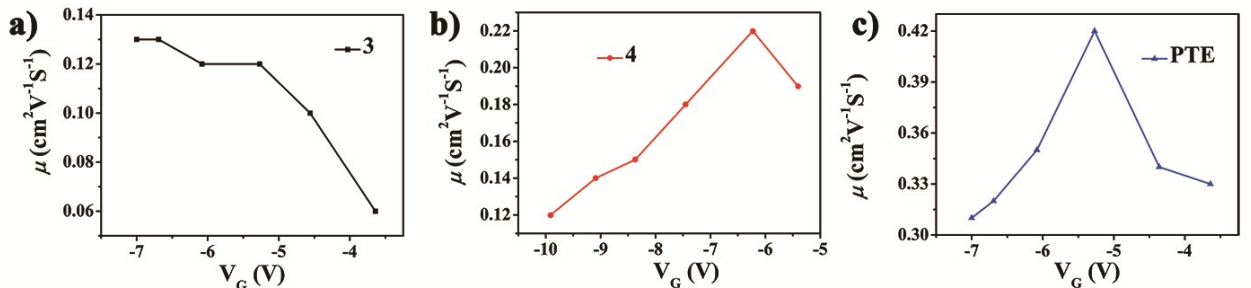


Fig. S20 The mobility plots versus gate voltages for (a) 3, (b) 4 and (c) PTE.